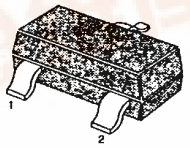
MMBC1622D7 NPN EPITAXIAL SILICON TRANSISTOR

T-29-19

AMPLIFIER TRANSISTOR

SOT-23



1. Base 2. Emitter 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	35	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	Tstg	150	°C

• Refer to MMBC1622D6 for graphs

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=25V, I_E=0		50	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0		50	nA
DC Current Gain	h_{FE}	V_{CE}=3V, I_C=0.1mA	150		
		V_{CE}=3V, I_C=0.5mA	300	600	
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=100mA, I_B=10mA		0.3	V
Base-Emitter On Voltage	V_{BE} (on)	I_C=0.5mA, V_{CE}=3V	0.55	0.65	V
Current Gain-Bandwidth Product	f_T	V_{CE}=6V, I_E=1mA f=100MHz	100		MHz

Marking